



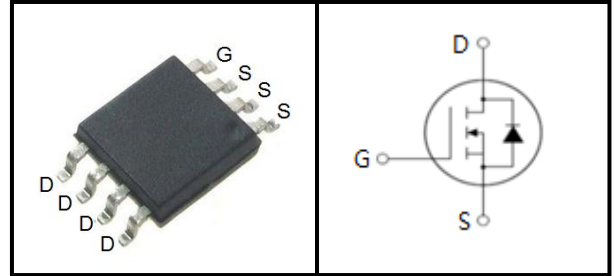
100V N-Channel DTMOS

FEATURES

- Trench Power DTMOS technology
- Low $R_{DS(ON)}$
- Low Gate Charge
- Optimized for fast-switching applications

APPLICATIONS

- Synchronous Rectification in DC/DC and AC/DC Converters
- Isolated DC/DC Converters in Telecom and Industrial



Device Marking and Package Information		
Device	Package	Marking
TSJ12N10A	SOP-8	12N10A

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted			
Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS} = 0\text{V}$)	V_{DSS}	100	V
Continuous Drain Current	I_D	11	A
Pulsed Drain Current (note1)	I_{DM}	44	A
Gate-Source Voltage	V_{GSS}	± 20	V
Single Pulse Avalanche Energy (note2)	E_{AS}	20	mJ
Avalanche Current (note1)	I_{AS}	20	A
Power Dissipation ($T_C = 25^\circ\text{C}$)	P_D	3.1	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55~+150	$^\circ\text{C}$

Thermal Resistance			
Parameter	Symbol	Value	Unit
Junction-to-Drain Lead	R_{thJC}	24	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient	R_{thJA}	40	



Specifications $T_J = 25^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 95V, V_{GS} = 0V, T_J = 25^\circ\text{C}$	--	--	1	μA
		$V_{DS} = 95V, V_{GS} = 0V, T_J = 150^\circ\text{C}$	--	--	100	
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20V$	--	--	± 100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.5	--	4	V
Drain-Source On-Resistance (Note3)	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 11.5A$	--	9	12	m Ω
Forward Transconductance (Note3)	g_{fs}	$V_{DS} = 5V, I_D = 11.5A$	--	45	--	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0V,$ $V_{DS} = 50V,$ $f = 1.0\text{MHz}$	--	2455	--	pF
Output Capacitance	C_{oss}		--	153	--	
Reverse Transfer Capacitance	C_{rss}		--	12	--	
Total Gate Charge	Q_g	$V_{DD} = 50V, I_D = 11.5A,$ $V_{GS} = 10V$	--	45	--	nC
Gate-Source Charge	Q_{gs}		--	13.5	--	
Gate-Drain Charge	Q_{gd}		--	11.5	--	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50V, I_D = 11.5A,$ $R_G = 3\Omega$	--	8	--	ns
Turn-on Rise Time	t_r		--	3	--	
Turn-off Delay Time	$t_{d(off)}$		--	25	--	
Turn-off Fall Time	t_f		--	4	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	$T_C = 25^\circ\text{C}$	--	--	4	A
Pulsed Diode Forward Current	I_{SM}		--	--	12	
Body Diode Voltage	V_{SD}	$T_J = 25^\circ\text{C}, I_{SD} = 1A, V_{GS} = 0V$	--	0.72	1	V
Reverse Recovery Time	t_{rr}	$I_F = 11.5A,$ $di_F/dt = 500A/\mu s$	--	25	--	ns
Reverse Recovery Charge	Q_{rr}		--	110	--	nC

Notes

1. Repetitive Rating: Pulse Width limited by maximum junction temperature
2. $I_{AS} = 20A, V_{DD} = 50V, R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 1\%$
4. When mounted on 1" in square copper board



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

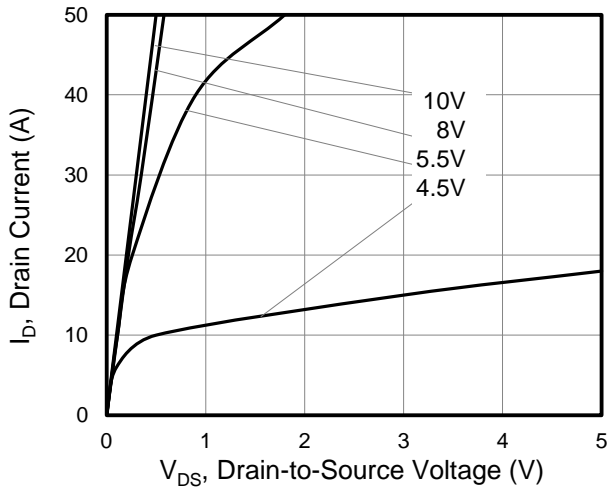


Figure 2. Transfer Characteristics

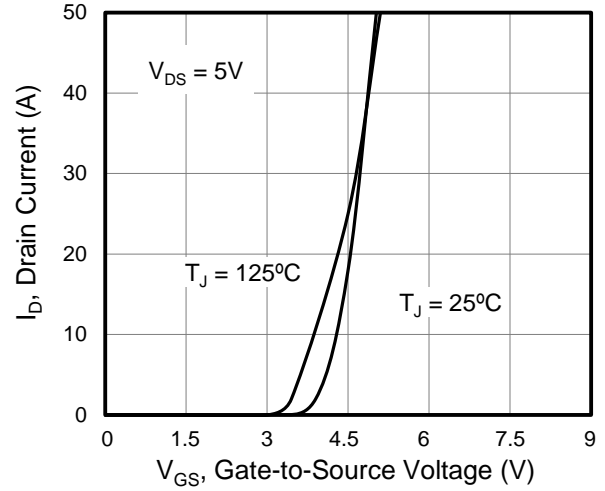


Figure 3. On-Resistance vs. Drain Current

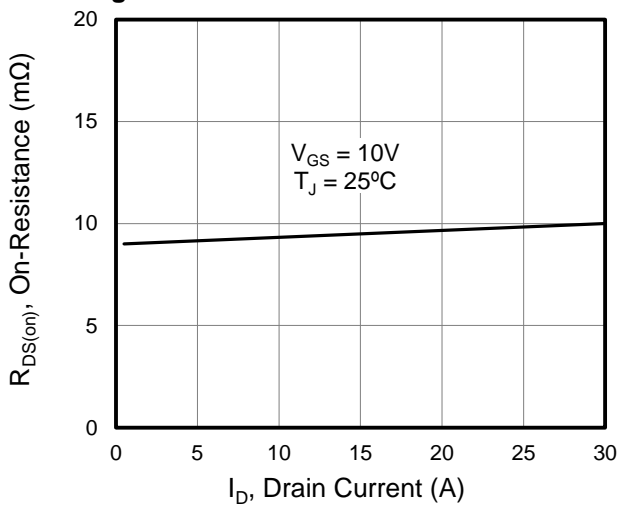


Figure 4. Capacitance

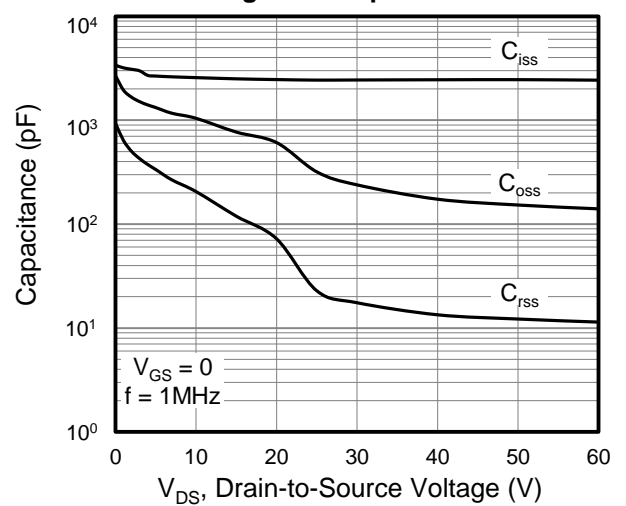


Figure 5. Gate Charge

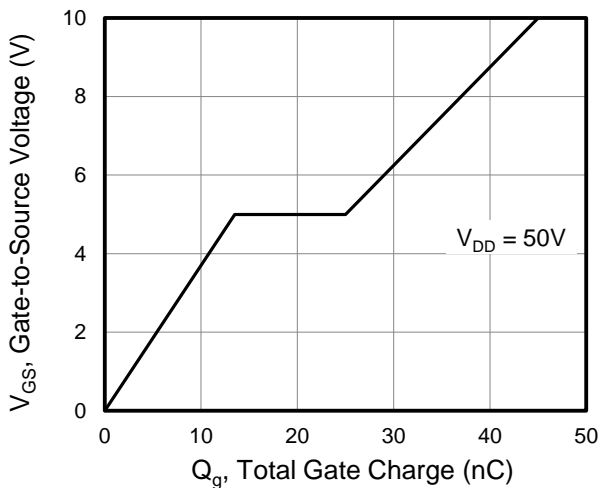
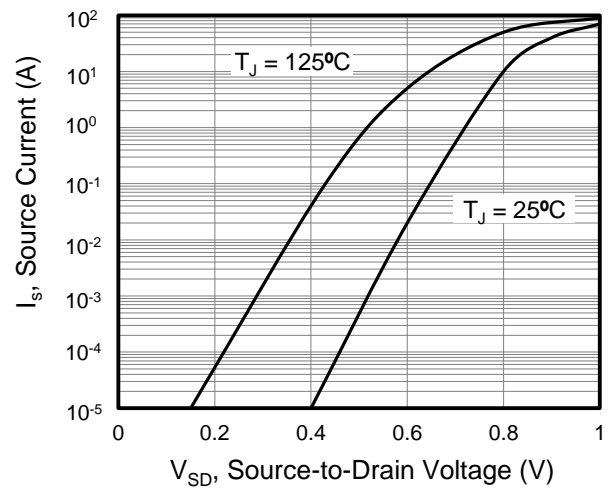


Figure 6. Body Diode Forward Voltage





Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. On-Resistance vs. Junction Temperature

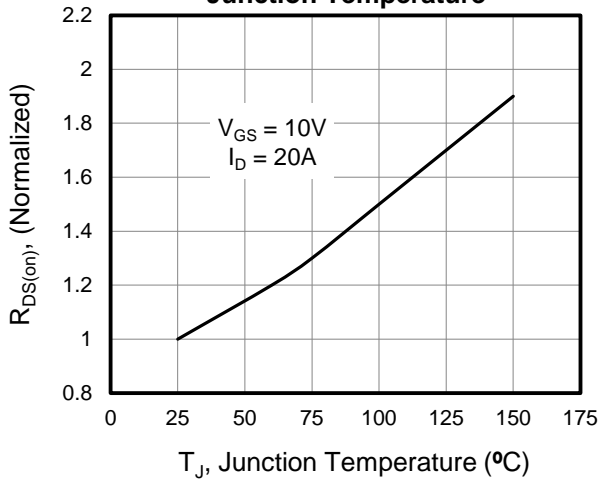


Figure 8. Threshold Voltage vs. Junction Temperature

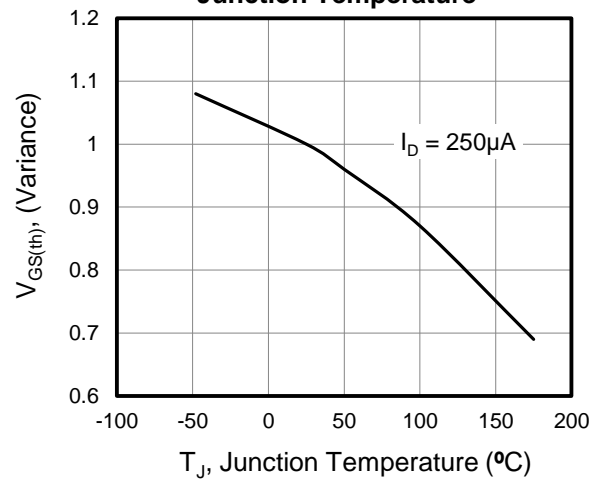


Figure 9. Transient Thermal Impedance

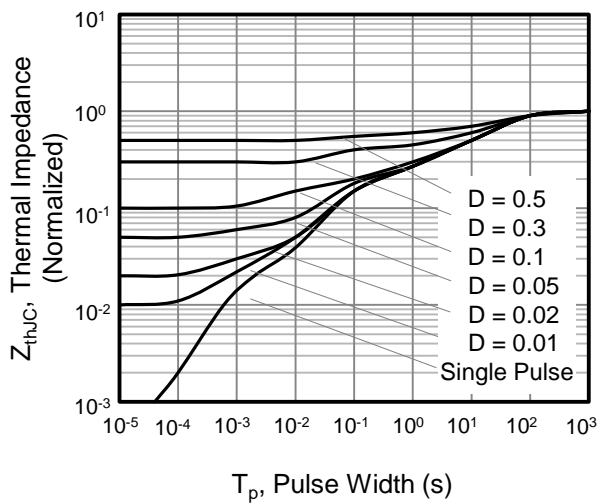




Figure A: Gate Charge Test Circuit and Waveform

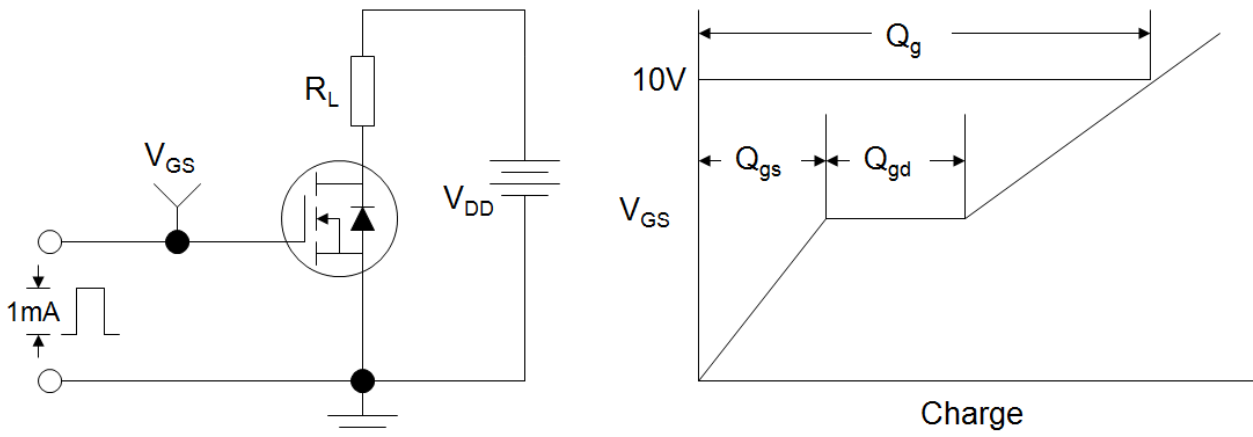
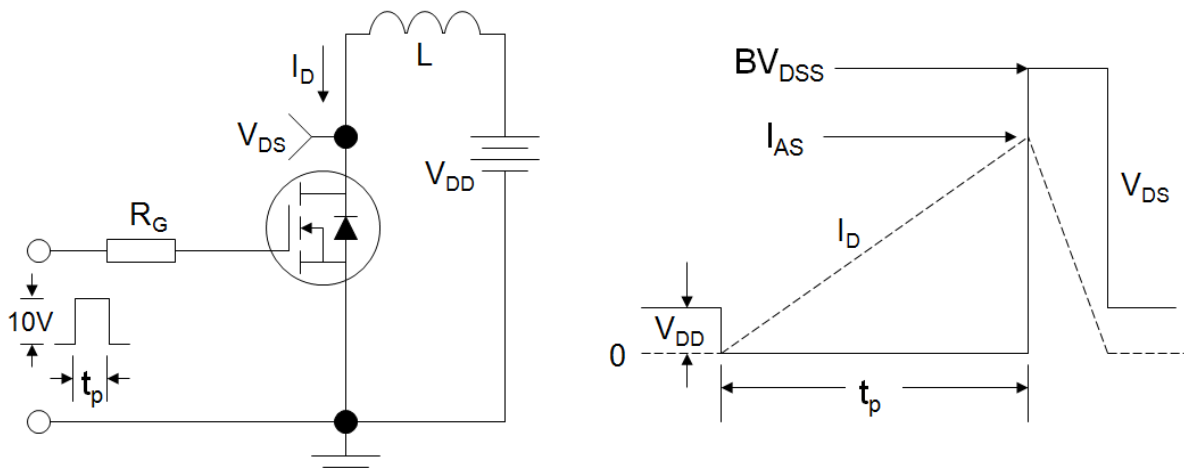


Figure B: Resistive Switching Test Circuit and Waveform



Figure C: Unclamped Inductive Switching Test Circuit and Waveform





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